



SHEET 1 OF 1

FORM PTO - 1449

INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-066

APPLICANT(S): Westhoff et al.

SERIAL NO.: 10/765,372

FILING DATE: January 27, 2004

GROUP: ~~2812~~ 2823

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>ABM</i>	A1	4,914,488	04/03/1990	Yamane et al			
	A2	4,960,728	10/02/1990	Schaake et al			
	A3	6,208,005	03/27/2001	Mitra			
	A4	6,515,335	02/04/2003	Christiansen et al			
	A5	2002/0185686	12/12/2002	Christiansen et al			

FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
<i>ABM</i>	C1	International Search Report for International Application No. PCT/US2004/002282 10/15/04

EXAMINER

ABMelson

DATE CONSIDERED

10/19/05



DEC 20 2004 FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-066 APPLICANT(S): Westhoff <i>et al.</i> SERIAL NO.: 10/765,372 FILING DATE: January 27, 2004 GROUP: ²⁸²³ 2812				
U.S. PATENT DOCUMENTS								
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>pbm</i>	A6	2001/0003364	06/14/2001	Sugawara <i>et al.</i> ✓	7			
	A7	2001/0014570	08/16/2001	Wenski <i>et al.</i> ✓				
	A8	2002/0043660	04/18/2002	Yamazaki <i>et al.</i> ✓				
	A9	2002/0084000	07/04/2002	Fitzgerald ✓				
	A10	2002/0096717	07/25/2002	Chu <i>et al.</i> ✓				
	A11	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i> ✓				
	A12	2002/0123167	09/05/2002	Fitzgerald ✓				
	A13	2002/0123183	09/05/2002	Fitzgerald ✓				
	A14	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i> ✓				
	A15	2002/0168864	11/14/2002	Cheng <i>et al.</i> ✓				
	A16	2002/0185686	12/12/2002	Christiansen <i>et al.</i>				
<i>pbm</i>	A17	2003/0003679	01/02/2003	Doyle <i>et al.</i> ✓		7		
	A18	2003/0013323	01/16/2003	Hammond <i>et al.</i> ✓				
	A19	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i> ✓				
	A20	2003/0041798	03/06/2003	Wenski <i>et al.</i> ✓				
	A21	2003/0057439	03/27/2003	Fitzgerald ✓				
	A22	2003/0102498	06/05/2003	Braithwaite <i>et al.</i> ✓				
	A23	2003/0199126	10/23/2003	Chu <i>et al.</i> ✓				
	A24	2003/0203600	10/30/2003	Chu <i>et al.</i> ✓				
	A25	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i> ✓				
	A26	2003/0218189	11/27/2003	Christiansen ✓				
	A27	2003/0227057	12/01/2003	Lochtefeld <i>et al.</i> ✓				
	A28	2004/0005740	01/01/2004	Lochtefeld <i>et al.</i> ✓				
	A29	2004/0014304	01/22/2004	Bhattacharyya ✓				
	A30	2004/0031979	02/19/2004	Lochtefeld ✓			06/06/2003	
	A31	2004/0041210	03/04/2004	Mouli ✓			09/02/2003	
EXAMINER <i>L. Melrose</i>				DATE CONSIDERED 10/19/2005				

* - Already listed on IDS (1449) filed on Nov. 5, 2004

FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-066 APPLICANT(S): Westhoff et al. SERIAL NO.: 10/765,372 FILING DATE: January 27, 2004 GROUP: 2823 <div style="text-align: right;">2842</div>			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
EOM		A32 2004/0075149	04/22/2004	Fitzgerald et al. ✓			07/23/2003
		A33 4,010,045	03/01/1977	Ruchrwein ✓			
		A34 4,710,788	12/01/1987	Dambkes et al. ✓			
		A35 4,900,372	02/13/1990	Lee et al. ✓			
		A36 4,987,462	01/22/1991	Kim et al. ✓			
		A37 4,990,979	02/05/1991	Otto ✓			
		A38 4,997,776	03/05/1991	Harame et al. ✓			
		A39 5,013,681	05/07/1991	Godbey et al. ✓			
		A40 5,091,767	02/25/1992	Bean et al. ✓			
		A41 5,097,630	03/24/1992	Maeda et al. ✓			
		A42 5,155,571	10/13/1992	Wang et al. ✓			
		A43 5,159,413	10/27/1992	Calviello et al. ✓			
		A44 5,166,084	11/24/1992	Pfiester ✓			
		A45 5,177,583	01/05/1993	Endo et al. ✓			
		A46 5,202,284	04/13/1993	Kamins et al. ✓			
		A47 5,207,864	05/04/1993	Bhat et al. ✓			
		A48 5,208,182	05/04/1993	Narayan et al. ✓			
		A49 5,210,052	05/11/1993	Takasaki ✓			
		A50 5,212,110	05/18/1993	Pfiester et al. ✓			
		A51 5,221,413	06/22/1993	Brasen et al. ✓			
		A52 5,240,876	08/31/1993	Gaul et al. ✓			
		A53 5,241,197	08/31/1993	Murakami et al. ✓			
		A54 5,250,445	10/05/1993	Bean et al. ✓			
		A55 5,252,173	10/12/1993	Inoue ✓			
		A56 5,279,687	01/18/1994	Tuppen et al. ✓			
		A57 5,285,086	02/08/1994	Fitzgerald ✓			
↓		A58 5,291,439	03/01/1994	Kauffmann et al. ✓			
EXAMINER <i>A. H. Malin</i>				DATE CONSIDERED <i>10/19/05</i>			

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INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Westhoff <i>et al.</i>			
				SERIAL NO.: 10/765,372			
				FILING DATE: January 27, 2004 GROUP: 2842 2823			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>dm</i>	A59	5,298,452	03/29/1994	Meyerson ✓			
	A60	5,308,444	05/03/1994	Fitz <i>et al.</i> ✓			
	A61	5,310,451	05/10/1994	Tejwani <i>et al.</i> ✓			
	A62	5,316,958	05/31/1994	Meyerson ✓			
	A63	5,346,848	09/13/1994	Gruppen-Shemansky <i>et al.</i> ✓			
	A64	5,374,564	12/20/1994	Bruel ✓			
	A65	5,399,522	03/21/1995	Ohori ✓			
	A66	5,413,679	05/09/1995	Godbey ✓			
	A67	5,424,243	06/13/1995	Takasaki ✓			
	A68	5,425,846	06/20/1995	Koze <i>et al.</i> ✓			
	A69	5,426,069	06/20/1995	Selvakumar <i>et al.</i> ✓			
	A70	5,426,316	06/20/1995	Mohammad ✓			
	A71	5,442,205	08/15/1995	Brasen <i>et al.</i> ✓			
	A72	5,461,243	10/24/1995	Ek <i>et al.</i> ✓			
	A73	5,461,250	10/24/1995	Burghartz <i>et al.</i> ✓			
	A74	5,462,883	10/31/1995	Dennard <i>et al.</i> ✓			
	A75	5,476,813	12/19/1995	Naruse ✓			
	A76	5,479,033	12/26/1995	Baca <i>et al.</i> ✓			
	A77	5,484,664	01/16/1996	Kitahara <i>et al.</i> ✓			
	A78	5,523,243	06/04/1996	Mohammad ✓			
	A79	5,523,592	06/04/1996	Nakagawa <i>et al.</i> ✓			
	A80	5,534,713	07/09/1996	Ismail <i>et al.</i> ✓			
	A81	5,536,361	07/16/1996	Kondo <i>et al.</i> ✓			
	A82	5,540,785	07/30/1996	Dennard <i>et al.</i> ✓			
	A83	5,572,043	11/05/1996	Shimizu <i>et al.</i> ✓			
	A84	5,596,527	01/21/1997	Tomioka <i>et al.</i> ✓			
✓	A85	5,617,351	04/01/1997	Bertin <i>et al.</i> ✓			
EXAMINER <i>A. Melson</i>				DATE CONSIDERED 10/19/05			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Exam</i>	A86	5,630,905	05/20/1997	Lynch et al. ✓			
	A87	5,633,516	05/27/1997	Mishima ✓			
	A88	5,659,187	08/01/1997	Legoues et al. ✓			
	A89	5,683,934	11/04/1997	Candelaria ✓			
	A90	5,698,869	12/16/1997	Yoshimi et al. ✓			
	A91	5,714,777	02/03/1998	Ismail et al. ✓			
	A92	5,728,623	03/17/1998	Mori ✓			
	A93	5,739,567	04/14/1998	Wong ✓			
	A94	5,759,898	06/02/1998	Ek et al. ✓			
	A95	5,777,347	07/07/1998	Bartelink ✓			
	A96	5,786,612	07/28/1998	Otani et al. ✓			
	A97	5,786,614	07/28/1998	Chuang et al. ✓			
	A98	5,792,679	08/11/1998	Nakato ✓			
	A99	5,801,085	09/01/1998	Kim et al. ✓			
	A100	5,808,344	09/15/1998	Ismail et al. ✓			
	A101	5,810,924	09/22/1998	Legoues et al. ✓			
	A102	5,828,114	10/27/1998	Kim et al. ✓			
	A103	5,847,419	12/08/1998	Imai et al. ✓			
	A104	5,859,864	01/12/1999	Jewell ✓			
	A105	5,877,070	03/02/1999	Goesele et al. ✓			
	A106	5,891,769	04/06/1999	Liaw et al. ✓			
	A107	5,906,708	05/25/1999	Robinson et al. ✓			
	A108	5,906,951	05/25/1999	Chu et al. ✓			
	A109	5,912,479	06/15/1999	Mori et al. ✓			
	A110	5,943,560	08/24/1999	Chang et al. ✓			
	A111	5,963,817	10/05/1999	Chu et al. ✓			
	A112	5,966,622	10/12/1999	Levine et al. ✓			
✓	A113	5,998,807	12/07/1999	Lustig et al. ✓			
EXAMINER <i>ABMabson</i>				DATE CONSIDERED <i>10/19/05</i>			

FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-066 APPLICANT(S): Westhoff et al. SERIAL NO.: 10/765,372 <div style="text-align: right; margin-right: 50px;">2823</div> FILING DATE: January 27, 2004 GROUP: 2812			
U.S. PATENT DOCUMENTS							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>Shm</i> <div style="border-left: 1px solid black; height: 100%; position: relative; margin-left: 10px;"> <div style="position: absolute; top: 0; left: -10px; width: 10px; height: 100%; border-left: 1px solid black;"></div> </div>	A114	6,010,937	01/04/2000	Karam et al. ✓	<div style="border-left: 1px solid black; height: 100%; position: relative;"> <div style="position: absolute; top: 0; left: -10px; width: 10px; height: 100%; border-left: 1px solid black;"></div> </div>		
	A115	6,013,134	01/11/2000	Chu et al. ✓			
	A116	6,030,884	02/29/2000	Mori ✓			
	A117	6,033,974	03/07/2000	Henley et al. ✓			
	A118	6,033,995	03/07/2000	Muller ✓			
	A119	6,039,803	03/21/2000	Fitzgerald et al. ✓			
	A120	6,058,044	05/02/2000	Sugiura et al. ✓			
	A121	6,059,895	05/09/2000	Chu et al. ✓			
	A122	6,074,919	06/13/2000	Gardner et al. ✓			
	A123	6,096,590	08/01/2000	Chan et al. ✓			
	A124	6,103,559	08/15/2000	Gardner et al. ✓			
	A125	6,107,653	08/22/2000	Fitzgerald ✓			
	A126	6,111,267	08/29/2000	Fischer et al. ✓			
	A127	6,117,750	09/12/2000	Bensahel et al. ✓			
	A128	6,124,617	09/26/2000	Ryum et al. ✓			
	A129	6,130,453	10/10/2000	Mei et al. ✓			
	A130	6,133,799	10/17/2000	Favors et al. ✓			
	A131	6,140,687	10/31/2000	Shimomura et al. ✓			
	A132	6,143,636	11/07/2000	Forbes et al. ✓			
	A133	6,153,495	11/28/2000	Kub et al. ✓			
	A134	6,154,475	11/28/2000	Soref et al. ✓			
A135	6,160,303	12/12/2000	Fattaruso ✓				
A136	6,162,688	12/19/2000	Gardner et al. ✓				
A137	6,184,111	02/06/2001	Henley et al. ✓				
A138	6,191,006	02/20/2001	Mori ✓				
A139	6,191,007	02/20/2001	Matsui et al. ✓				
A140	6,191,432	02/20/2001	Sugiyama et al. ✓				
✓	A141	6,194,722	02/27/2001	Fiorini et al. ✓			
EXAMINER <i>Shm</i>				DATE CONSIDERED 10/19/05			

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U.S. PATENT DOCUMENTS							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
<i>Abm</i> ↓	A142	6,204,529	Lung <i>et al.</i> ✓				
	A143	6,207,977	Augusto ✓				
	A144	6,210,988	Howe <i>et al.</i> ✓				
	A145	6,218,677	Broekaert ✓				
	A146	6,232,138	Fitzgerald <i>et al.</i> ✓				
	A147	6,235,567	Huang ✓				
	A148	6,242,324	Kub <i>et al.</i> ✓				
	A149	6,249,022	Lin <i>et al.</i> ✓				
	A150	6,251,755	Furukawa <i>et al.</i> ✓				
	A151	6,261,929	Gehrke <i>et al.</i> ✓				
	A152	6,266,278	Harari <i>et al.</i> ✓				
	A153	6,271,551	Schmitz <i>et al.</i> ✓				
	A154	6,271,726	Fransis <i>et al.</i> ✓				
	A155	6,291,321	Fitzgerald ✓				
	A156	6,313,016	Kibbel <i>et al.</i> ✓				
	A157	6,316,301	Kant ✓				
	A158	6,323,108	Kub <i>et al.</i> ✓				
	A159	6,329,063	Lo <i>et al.</i> ✓				
	A160	6,335,546	Tsuda <i>et al.</i> ✓				
A161	6,339,232	Takagi ✓					
A162	6,350,993	Chu <i>et al.</i> ✓					
A163	6,352,909	Usenko ✓					
A164	6,368,733	Nishinaga ✓					
A165	6,372,356	Thornton <i>et al.</i> ✓					
A166	6,399,970	Kubo <i>et al.</i> ✓					
A167	6,403,975	Brunner <i>et al.</i> ✓					
A168	6,406,589	Yanagisawa ✓					
A169	6,407,406	Tezuka ✓					
EXAMINER <i>Abm</i>				DATE CONSIDERED <i>10/19/05</i>			

FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-066			
INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Westhoff <i>et al.</i>			
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				FILING DATE: January 27, 2004 GROUP: 2812 ²⁸²³			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Abm</i>	A170	6,420,937	07/16/2002	Akatsuka <i>et al.</i> ✓			
	A171	6,425,951	07/30/2002	Chu <i>et al.</i> ✓			
	A172	6,429,061	08/06/2002	Rim ✓			
	A173	6,482,749	11/19/2002	Billington <i>et al.</i> ✓			
	A174	6,518,644	02/11/2003	Fitzgerald ✓			
	A175	6,521,041	02/18/2003	Wu <i>et al.</i> ✓			
	A176	6,524,935	02/25/2003	Canaperi <i>et al.</i> ✓			
	A177	6,525,338	02/25/2003	Mizushima <i>et al.</i> ✓			
	A178	6,555,839	04/29/2003	Fitzgerald ✓			
	A179	6,573,126	06/03/2003	Cheng <i>et al.</i> ✓			
	A180	6,576,532	06/10/2003	Jones <i>et al.</i> ✓			
	A181	6,583,015	06/24/2003	Fitzgerald <i>et al.</i> ✓			
	A182	6,593,191	07/15/2003	Fitzgerald ✓			
	A183	6,594,293	07/15/2003	Bulsara <i>et al.</i> ✓			
	A184	6,602,613	08/05/2003	Fitzgerald ✓			
	A185	6,603,156	08/05/2003	Rim ✓			
	A186	6,646,322	11/11/2003	Fitzgerald ✓			
	A187	6,649,480	11/18/2003	Fitzgerald <i>et al.</i> ✓			
	A188	6,677,192	01/13/2004	Fitzgerald ✓			
	A189	6,703,144	03/09/2004	Fitzgerald ✓			03/18/2003
	A190	6,703,688	03/09/2004	Fitzgerald ✓			07/16/2001
	A191	6,709,903	03/23/2004	Christiansen ✓			04/30/2003
	A192	6,713,326	03/30/2004	Cheng <i>et al.</i> ✓			03/04/2003
	A193	6,723,661	04/20/2004	Fitzgerald ✓			07/16/2001
	A194	6,724,008	04/20/2004	Fitzgerald ✓			07/16/2001
	A195	6,730,551	05/04/2004	Lee <i>et al.</i> ✓			08/02/2002
	A196	6,737,670	05/18/2004	Cheng <i>et al.</i> ✓			03/07/2003
	A197	6,750,130	06/15/2004	Fitzgerald ✓			01/07/2001
EXAMINER <i>Abm</i>				DATE CONSIDERED <i>10/19/05</i>			

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U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
FOREIGN PATENT DOCUMENTS									
EXAM INIT.		DOCUMENT NUMBER	DATE	COUN- TRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>Alm</i>	B1	41 01 167	07/23/1992	DE ✓				N	Y (Abstract only)
	B2	0 514 018	11/19/1992	EP ✓				N	Y
	B3	0 587 520	03/16/1994	EP ✓				N	Y
	B4	0 683 522	11/22/1995	EP ✓				N	Y
	B5	0 828 296	03/11/1998	EP ✓				N	Y
	B6	0 829 908	03/18/1998	EP ✓				N	Y
	B7	0 838 858	04/29/1998	EP ✓				N	Y (Abstract only)
	B8	1 020 900	07/19/2000	EP ✓				N	Y
	B9	1 174 928	01/23/2002	EP ✓				N	Y
	B10	2 342 777	04/19/2000	GB ✓				Y	Y
	B11	2-210816	08/22/1990	JP ✓				N	Y (Abstract only)
	B12	3-36717	02/18/1991	JP ✓				N	N
	B13	4-307974	10/30/1992	JP ✓				N	N
	B14	5-166724	07/02/1993	JP ✓				N	Y (Abstract only)
	B15	6-177046	06/24/1994	JP ✓				N	Y (Abstract only)
	B16	6-244112	09/02/1994	JP ✓				Y	Y
	B17	6-252046	09/09/1994	JP ✓				Y	Y
	B18	7-94420	04/07/1995	JP ✓				N	Y (Abstract only)
	B19	7-106446	04/21/1995	JP ✓				N	N
	B20	7-240372	09/12/1995	JP ✓				N	Y (Abstract only)
	B21	10-270685	10/09/1998	JP ✓				N	Y
	B22	11-233744	08/27/1999	JP ✓				N	N
EXAMINER <i>Alm</i>					DATE CONSIDERED 10/19/05				

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<i>pm</i>	B23	61-141116	06/28/1986	JP	/		N	Y (Abstract only)
	B24	2000-021783	01/21/2000	JP	/		N	Y
	B25	2000-031491	01/28/2000	JP	/		N	Y
	B26	2000-513507	10/10/2000	JP	/		Y	N
	B27	2001-319935	11/16/2001	JP	/		N	Y
	B28	2002-076334	03/15/2002	JP	/		N	Y
	B29	2002-164520	06/07/2002	JP	/		N	Y
	B30	2002-289533	10/04/2002	JP	/		N	Y
	B31	2002-356399	12/13/2002	JP	/		Y	Y
	B32	98/59365	12/30/1998	WO	/		N	Y
	B33	99/53539	10/21/1999	WO	/		N	Y
	B34	00/48239	08/17/2000	WO	/		N	Y
	B35	00/54338	09/14/2000	WO	/		N	Y
	B36	01/022482	03/29/2001	WO	/		N	Y
	B37	01/54175	07/26/2001	WO	/		N	Y
	B38	01/54202	07/26/2001	WO	/		N	Y
	B39	01/93338	12/06/2001	WO	/		N	Y
	B40	01/99169	12/27/2001	WO	/		N	Y
	B41	02/013262	02/14/2002	WO	/		N	Y
	B42	02/015244	02/21/2002	WO	/		N	Y
<i>↓</i>	B43	02/027783	04/04/2002	WO	/		N	Y

EXAMINER

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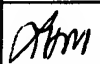


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FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT				ATTORNEY DOCKET NO.: ASC-066 APPLICANT(S): Westhoff <i>et al.</i> SERIAL NO.: 10/765,372 FILING DATE: January 27, 2004 GROUP: 2812 ²⁸²³					
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Am	B44	02/047168 ✓	06/13/2002	WO				N	Y
	B45	02/071488 ✓	09/12/2002	WO				N	Y
	B46	02/071491 ✓	09/12/2002	WO				N	Y
	B47	02/071495 ✓	09/12/2002	WO				N	Y
	B48	02/082514 ✓	10/17/2002	WO				N	Y
	B49	03/015140 ✓	02/20/2003	WO				N	Y (Abstract only)
	B50	04/006311 ✓	01/15/2004	WO				N	Y
↓	B51	04/006327 ✓	01/15/2004	WO				N	Y
OTHER ART, JOURNAL ARTICLES, ETC.									
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Am	C2	Armstrong <i>et al.</i> , "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEDM Technical Digest (1995 International Electron Devices Meeting)</u> , pp. 761-764.							
	C3	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," PhD Thesis, Massachusetts Institute of Technology, 1999, pp. 1-154.							
	C4	Augusto <i>et al.</i> , "Proposal for a New Process Flow for the Fabrication of Silicon-Based Complementary MOD-MOSFETs without Ion Implantation," <u>Thin Solid Films</u> , Vol. 294, No. 1-2 (February 15, 1997), pp. 254-258.							
	C5	Barradas <i>et al.</i> , "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," <u>Modern Physics Letters B</u> , Vol. 15 (2001), abstract.							
	C6	Borenstein <i>et al.</i> , "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMS) (January 17-21, 1999), pp. 205-210.							
↓	C7	Bouillon <i>et al.</i> , "Search for the optimal channel architecture for 0.18/0.12 μm bulk CMOS experimental study," <u>IEEE</u> (1996), pp. 21.2.1-21.2.4.							
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	C8	Briel <i>et al.</i> , "©SMART CUT: A Promising New SOI Material Technology," Proceedings of the 1995 IEEE International SOI Conference (October 1995), pp. 178-179.							
	C9	Briel, "Silicon on Insulator Material Technology," <u>Electronic Letters</u> , Vol. 13, No. 14 (July 6, 1995), pp. 1201-1202.							
	C10	Bulfer <i>et al.</i> , "Hole transport in strained Si _{1-x} Ge _x alloys on Si _{1-x} Ge _x substrates," <u>Journal of Applied Physics</u> , Vol. 84, No. 10 (November 15, 1998), pp. 5597-5602.							
	C11	Bulsara, "Materials Issues with the Integration of Lattice-Mismatched In _x Ga _{1-x} As on GaAs," PhD Thesis, MIT, June 1998, pp. 1-178.							
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	C19	Charasse <i>et al.</i> , "MBE Growth of GaAs on Si at Thomson," <u>IEE Colloquium on GaAs on Si</u> , (8 Mar 1988), pp. 1-4							
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
Am	C20	Cheng <i>et al.</i> , "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001), pp. 321-323.							
	C21	Cheng <i>et al.</i> , "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," <u>Journal of Electronic Materials</u> , Vol. 30, No. 12 (2001), pp. L37-L39.							
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	C25	Currie <i>et al.</i> , "Controlling Threading Dislocation Densities in Ge on Si Using Graded SiGe Layers and Chemical-Mechanical Polishing," <u>Applied Physics Letters</u> , Vol. 72, Issue 14 (04/06/98), pp. 1718-1720.							
	C26	Currie, "SiGe Virtual Substrate Engineering for Integration of III-V Materials, Microelectromechanical Systems and Strained Silicon Mosfets with Silicon," PhD Thesis, MIT, 2001, pp. 1-190.							
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	C30	Feichtinger <i>et al.</i> , "Misfit Dislocation Nucleation Study in p/p+ Silicon," <u>Journal of the Electrochemical Society</u> , 148 (7) (2001), pp. G379-G382.							
	C31	Feijoo <i>et al.</i> , "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," <u>Journal of Electronic Materials</u> , Vol. 23, No. 6 (June 1994), pp. 493-496.							
↓	C32	Fischetti <i>et al.</i> , "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," <u>Journal of Applied Physics</u> , Vol. 80, No. 4 (August 15, 1996), pp. 2234-2252.							
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	C35	Fitzgerald <i>et al.</i> , "Dislocation dynamics in relaxed graded composition semiconductors," <u>Materials Science and Engineering</u> , B67 (1999), pp. 53-61.							
	C36	Fitzgerald <i>et al.</i> , "GeSi/Si Nanostructures," <u>Department of Materials Science, M.I.T.</u> , (1995), pp. 1-15.							
	C37	Fitzgerald <i>et al.</i> , "Relaxed Ge _x Si _{1-x} structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," <u>American Vacuum Society</u> , (1992) pp. 1807-1819.							
	C38	Fitzgerald <i>et al.</i> , "Totally Relaxed Ge _x Si _{1-x} Layers with Low Threading Dislocation Densities Grown on Si Substrates," <u>Applied Physics Letters</u> , Vol. 59, No. 7 (August 12, 1991), pp. 811-813.							
	C39	Garone <i>et al.</i> , "Silicon vapor phase epitaxial growth catalysis by the presence of germane," <u>Applied Physics Letters</u> , Vol. 56, No. 13 (March 26, 1990), pp. 1275-1277.							
	C40	Giovane <i>et al.</i> , "Strain-Balanced Silicon-Germanium Materials for Near IR Photodetection in Silicon-Based Optical Interconnects," PhD Thesis, MIT, 1998, pp. 1-134.							
	C41	Godbey <i>et al.</i> , "Fabrication of Bond and Etch-Back Silicon Insulator Using a Strained Si0.7Ge0.3 Layer as an Etch Stop," <u>Journal of the Electrical Society</u> , Vol. 137, No. 10 (October 1990) pp. 3219-3223.							
	C42	Gray <i>et al.</i> , "Analysis and Design of Analog Integrated Circuits," John Wiley & Sons, 1984, pp. 605-632.							
	C43	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in (Al _x Ga _{1-x}) _{0.5} In _{0.5} P heterostructures," <u>Journal of Applied Physics</u> , Vol. 91, No. 8 (April 15, 2002), pp. 4891-4899.							
	C44	Groenert <i>et al.</i> , "Strategies for Direct Monolithic Integration of Al _x Ga _(1-x) As/In _x Ga _(1-x) As LEDS and Lasers on Ge/GeSi/Si Substrates Via Relaxed Graded Ge _x Si _(1-x) Buffer Layers," <u>Materials Research Society Symposium Proceedings</u> , Vol. 692 (2002), pp. H.9.30.1-H.9.30.6.							
	C45	Grützmaier <i>et al.</i> , "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," <u>Applied Physics Letters</u> , Vol. 63, No. 18 (November 1, 1993), pp. 2531-2533.							
	C46	Hackbarth <i>et al.</i> , "Alternatives to thick MBE-grown relaxed SiGe buffers," <u>Thin Solid Films</u> , Vol. 369, No. 1-2 (July 2000), pp. 148-151.							
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<div style="text-align: center;">  </div> <div style="border-left: 1px solid black; height: 100px; margin-left: 10px;"></div> <div style="text-align: center;">  </div>	C47 C48 C49 C50 C51 C52 C53 C54 C55 C56 C57 C58 C59	<p>Hackbarth <i>et al.</i>, "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," <u>Journal of Crystal Growth</u>, Vol. 201/202 (1999), pp. 734-738.</p> <p>Halsall <i>et al.</i>, "Electron diffraction and Raman studies of the effect of substrate misorientation on ordering in the AlGaInP system," <u>Journal of Applied Physics</u>, Vol. 85, No. 1 (Jan. 1999), pp. 199-202</p> <p>Herzog <i>et al.</i>, "SiGe-based FETs: buffer issues and device results," <u>Thin Solid Films</u>, Vol. 380 (2000), pp. 36-41.</p> <p>Höck <i>et al.</i>, "Carrier mobilities in modulation doped Si_{1-x}Ge_x heterostructures with respect to FET applications," <u>Thin Solid Films</u>, Vol. 336 (1998), pp. 141-144.</p> <p>Höck <i>et al.</i>, "High hole mobility in Si_{0.17}Ge_{0.83} channel metal-oxide-semiconductor field-effect transistors grown by plasma-enhanced chemical vapor deposition," <u>Applied Physics Letters</u>, Vol. 76, No. 26 (June 26, 2000), pp. 3920-3922.</p> <p>Höck <i>et al.</i>, "High performance 0.25 μm p-type Ge/SiGe MODFETs," <u>Electronics Letters</u>, Vol. 34, No. 19 (September 17, 1998), pp. 1888-1889.</p> <p>Houghton, "Strain Relaxation Kinetics in Si_{1-x}Ge_x/Si Heterostructures," <u>Journal of Applied Physics</u>, Vol. 70, No. 4 (August 15, 1991), pp. 2136-2151.</p> <p>Hsu <i>et al.</i>, "Near Field Scanning Optical Microscopy Studies of Electronic and Photonic Materials and Devices," <u>Materials Science and Engineering Reports: A Review Journal</u>, Vol. 33 (2001), pp. 1-50.</p> <p>Hsu <i>et al.</i>, "Surface morphology of related Ge_xSi_{1-x} films," <u>Applied Physics Letters</u>, 61 (11) (September 14, 1992), pp. 1293-1295.</p> <p>Huang <i>et al.</i>, (2001) "Carrier Mobility enhancement in strained Si-on-insulator fabricated by wafer bonding", <u>2001 Symposium on VLSI Technology. Digest of Technical Papers</u>, pages 57-58</p> <p>Huang <i>et al.</i>, "High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate," <u>Applied Physics Letters</u>, Vol. 76, No. 19 (May 8, 2000), pp. 2680-2682.</p> <p>Huang <i>et al.</i>, "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits," <u>IEEE Journal of Solid-State Circuits</u>, Vol. 33, No. 7 (July 1998), pp. 1023-1036.</p> <p>Ishikawa <i>et al.</i>, "Creation of Si-Ge-based SIMOX structures by low energy oxygen implantation," <u>Proceedings of the 1997 IEEE International SOI Conference</u> (October 1997), pp. 16-17.</p>							
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	C61	Ismail <i>et al.</i> , "Modulation-doped n-type Si/SiGe with inverted interface," <u>Applied Physics Letters</u> , Vol. 65, No. 10 (September 5, 1994), pp. 1248-1250.							
	C62	Ismail, "Si/SiGe High-Speed Field-Effect Transistors," Electron Devices Meeting, Washington, D.C. (December 10, 1995), pp. 20.1.1-20.1.4.							
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	C64	Kim <i>et al.</i> , "A Fully Integrated 1.9-GHz CMOS Low-Noise Amplifier," <u>IEEE Microwave and Guided Wave Letters</u> , Vol. 8, No. 8 (August 1998), pp. 293-295.							
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	C67	Koester <i>et al.</i> , "Extremely High Transconductance Ge/Si _{0.4} Ge _{0.6} p-MODFET's Grown by UHV-CVD," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 3 (March 2000), pp. 110-112.							
	C68	König <i>et al.</i> , "Design Rules for n-Type SiGe Hetero FETs," <u>Solid State Electronics</u> , Vol. 41, No. 10 (1997), pp. 1541-1547.							
	C69	König <i>et al.</i> , "p-Type Ge-Channel MODFET's with High Transconductance Grown on Si Substrates," <u>IEEE Electron Device Letters</u> , Vol. 14, No. 4 (April 1993), pp. 205-207.							
	C70	König <i>et al.</i> , "SiGe HBTs and HFETs," <u>Solid-State Electronics</u> , Vol. 38, No. 9 (1995), pp. 1595-1602.							
	C71	Kummer <i>et al.</i> , "Low energy plasma enhanced chemical vapor deposition," <u>Materials Science and Engineering</u> , B89 (2002), pp. 288-295.							
	C72	Kuznetsov <i>et al.</i> , "Technology for high-performance n-channel SiGe modulation-doped field-effect transistors," <u>Journal of Vacuum Science and Technology</u> , B 13(6) (November/December 1995), pp. 2892-2896.							
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<i>abm</i>	C73	Langdo, "High Quality Ge on Si by Epitaxial Necking," <u>Applied Physics Letters</u> , Vol. 76, Issue 25 (June 19, 2000), pp. 3700-3702.							
	C74	Langdo et al., (2002) "Preparation of Novel SiGe-free Strained Si on Insulator Substrates" <u>IEEE International SOI Conference</u> , pages 211-212 (XP002263057)							
	C75	Larson, "Integrated Circuit Technology Options for RFIC's Present Status and Future Directions," <u>IEEE Journal of Solid-State Circuits</u> , Vol. 33, No. 3 (March 1998), pp. 387-399.							
	C76	Lee <i>et al.</i> , "CMOS RF Integrated Circuits at 5 GHz and Beyond," <u>Proceedings of the IEEE</u> , Vol. 88, No. 10 (October 2000), pp. 1560-1571.							
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	C82	Leitz <i>et al.</i> , "Hole mobility enhancements in strained Si/Si _{1-y} Ge _y p-type metal-oxide-semiconductor field-effect transistors grown on relaxed Si1-xGex (x<y) virtual substrates," <u>Applied Physics Letters</u> , Vol. 79, No. 25 (December 17, 2001), pp. 4246-4248.							
	C83	Li <i>et al.</i> , "Design of high speed Si/SiGe heterojunction complementary metal-oxide-semiconductor field effect transistors with reduced short-channel effects," <u>Journal of Vacuum Science and Technology A</u> , Vol. 20, No.3 (May/June 2002), pp. 1030-1033.							
↓	C84	Liu <i>et al.</i> , "Growth Study of Surfactant-Mediated Relaxed SiGe Graded Layers for 1.55-μm Photodetector Applications," <u>Thin Solid Films</u> , Vol. 380, Issue 1-2 (2000), pp. 54-56.							
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				FILING DATE: January 27, 2004 GROUP: 2812 ²⁸²³					
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	C89	Maiti <i>et al.</i> , "Strained-Si heterostructure field effect transistors," <u>Semiconductor Science and Technology</u> , Vol. 13 (1998), pp. 1225-1246.							
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	C94	Mizuno <i>et al.</i> , "High Performance Strained-Si p-MOSFETs on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE IDEM Technical Digest</u> (1999 International Electron Device Meeting), pp. 934-936.							
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	C102	Papananos, "Radio-Frequency Microelectronic Circuits for Telecommunication Applications," Kluwer Academic Publishers, 1999, pp. 115-117, 188-193.							
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	C104	Powell <i>et al.</i> , "New Approach to the Growth of Low Dislocation Relaxed SiGe Material," <u>Applied Physics Letters</u> , Vol. 64, Issue 14 (April 4, 1994), pp. 1856-1858.							
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↓	C108	Rim <i>et al.</i> , "Enhanced Hole Mobilities in Surface-Channel Strained-Si p-MOSFETs," <u>IEDM</u> (1995), pp. 517-520.							
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<div style="text-align: center;"> ↓ </div>	C109 C110 C111 C112 C113 C114 C115 C116 C117 C118 C119 C120 C121	<p>Rim <i>et al.</i>, "Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET's," <u>IEEE Transactions on Electron Devices</u>, Vol. 47, No. 7 (July 2000), pp. 1406-1415.</p> <p>Robbins <i>et al.</i>, "A model for heterogeneous growth of Si_{1-x}Ge_x films for hydrides," <u>Journal of Applied Physics</u>, Vol. 69, No. 6 (March 15, 1991), pp. 3729-3732.</p> <p>Sadek <i>et al.</i>, "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEEE Transactions on Electron Devices</u> (August 1996), pp. 1224-1232.</p> <p>Sakaguchi <i>et al.</i>, "ELTRAN® by Splitting Porous Si Layers," <u>Proceedings of the 195th International SOI Symposium</u>, Vol. 99-3 (1999), pp. 117-121.</p> <p>Sakai <i>et al.</i>, "Reduction of Threading Dislocation Density in SiGe Layers on Si (001) Using a Two-Step Strain - Relaxation Procedure," <u>Applied Physics Letters</u>, Vol. 79, Issue 21 (November 19, 2001), pp. 3398-3400.</p> <p>Samavedam <i>et al.</i>, "Novel Dislocation Structure and Surface Morphology Effects in Relaxed Ge/Si-Ge (graded) / Si Structures," <u>Journal of Applied Physics</u>, Vol. 87, Issue 7 (April 1, 1997), pp. 3108-3116.</p> <p>Schäffler, "High-Mobility Si and Ge Structures," <u>Semiconductor Science and Technology</u>, Vol. 12 (1997), pp. 1515-1549.</p> <p>Schimmel, "Defect Etch for <100> Silicon Evaluation," <u>Journal of the Electrochemical Society</u>, Vol. 126, No. 3 (March 1979), pp. 479-482.</p> <p>Sugimoto <i>et al.</i>, "A 2V, 500 MHz and 3V, 920 MHz Low-Power Current-Mode 0.6 μm CMOS VCO Circuit," <u>IEICE Trans Electron</u>, Vol. E82-C, No. 7 (July 1999), pp. 1327-1329.</p> <p>Taylor <i>et al.</i>, "Optoelectronic Device Performance on Reduced Threading Dislocation Density GaAs/Si," <u>American Institute of Physics</u>, Vol. 89, Issue 8 (April 15, 2001), pp. 4365-4375.</p> <p>Ternent <i>et al.</i>, "Metal Gate Strained Silicon MOSFETs for Microwave Integrated Circuits," <u>IEEE</u> (October 2000), pp. 38-43.</p> <p>Ting <i>et al.</i>, "Monolithic Integration of III-V Materials and Devices on Silicon," <u>SPIE Conference 1999- Silicon Based Optoelectronics</u>, Vol. 3630 (Jan 1999), pp. 19-28.</p> <p>Tsang <i>et al.</i>, "Measurements of alloy composition and strain in thin Ge_xSi_{1-x} layers," <u>Journal of Applied Physics</u>, Vol. 75, No. 12 (June 15, 1994), pp. 8098-8108.</p>								
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